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6/19/02

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Fumitaka Sugaya

Serial No.: 09/387,857

Art Unit: 2822

Filed: September 1, 1999

Examiner: C. Novacek

For: A SEMICONDUCTOR DEVICE AND A
METHOD OF MANUFACTURING THE
SAME

Atty Docket: 21776/0039

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RESPONSE AND AMENDMENT UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated March 14, 2002, please amend the above-captioned application as follows:

IN THE SPECIFICATION:

Pages 6-7, paragraph 2 should read

C1
A method of fabricating a semiconductor device according to the present invention comprises the first step of defining an element active region by forming an element isolation structure on a semiconductor substrate, the second step of forming an insulating film on the semiconductor substrate in the element active region, the third step of forming a first conductive film on an entire surface of the semiconductor substrate including the insulating film and the element isolation structure, the fourth step of forming a mask pattern having first and second openings on the first conductive film, the fifth step of etching the first conductive film until the element isolation structure is exposed in the first opening by using the mask pattern as a mask, thereby dividing the first conductive film, and simultaneously forming a recess in the second opening having the first